

BIPOLAR TRANSISTOR (PNP)
FEATURES

Low equivalent on-resistance

Marking :591
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1	A
P _C	Collector Power Dissipation	500	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

FMMT591 (PNP)

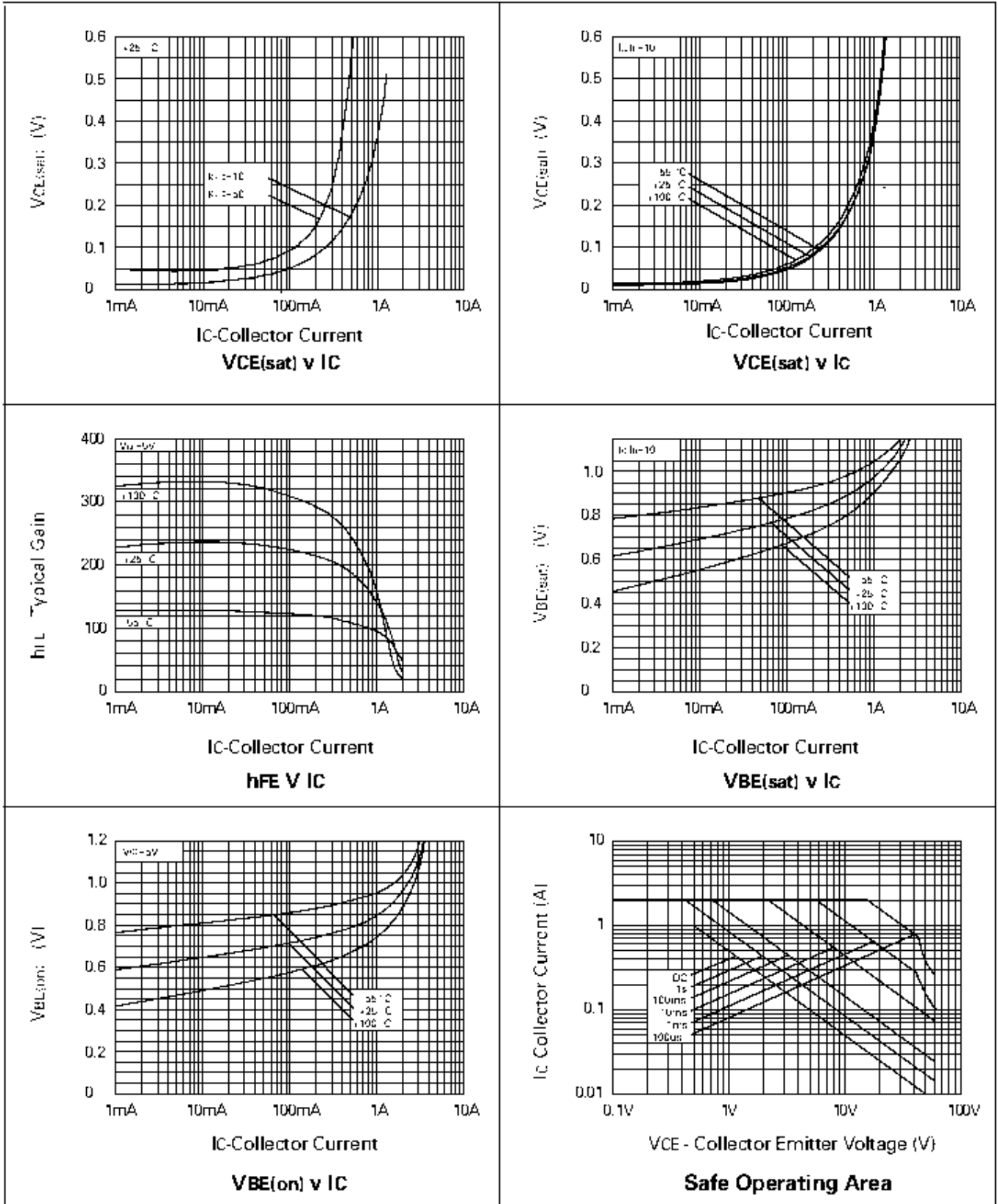
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

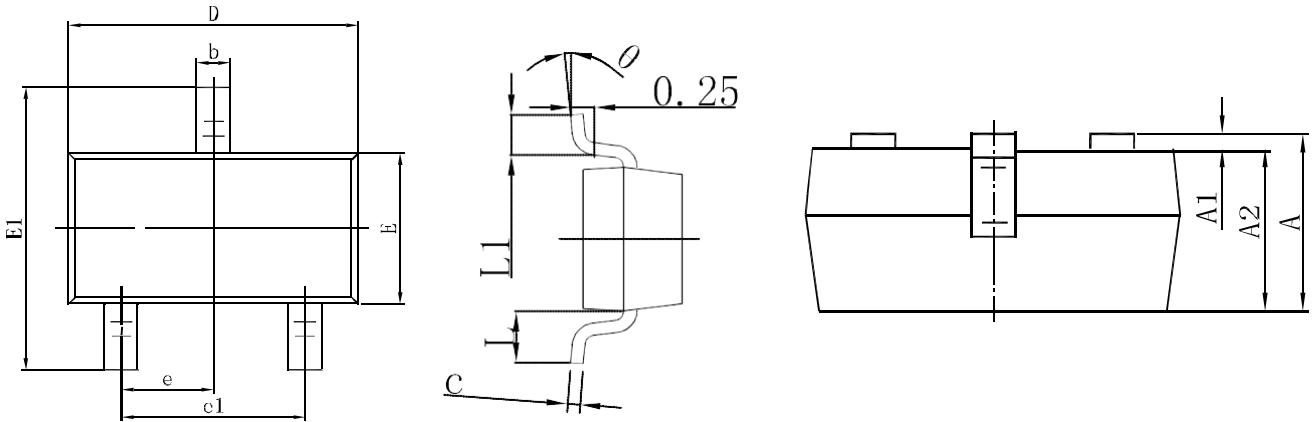
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO} ¹	I _C =-10mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-5V, I _C =-1mA	100			
	h _{FE(2)} ¹	V _{CE} =-5V, I _C =-500mA	100		300	
	h _{FE(3)} ¹	V _{CE} =-5V, I _C =-1A	80			
	h _{FE(4)} ¹	V _{CE} =-5V, I _C =-2A	15			
Collector-emitter saturation voltage	V _{CE(sat)1} ¹	I _C =-500mA, I _B =-50mA			-0.3	V
	V _{CE(sat)2} ¹	I _C =-1A, I _B =-100mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)} ¹	I _C =-1A, I _B =-100mA			-1.2	V
Base-emitter voltage	V _{BE} ¹	V _{CE} =-5V, I _C =-1A			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=100MHz	150			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, f=1MHz			10	pF

¹Measured under pulsed conditions, Pulse width=300μs, Duty cycle≤2%.

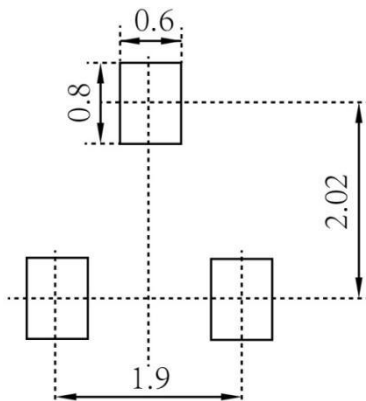
BIPOLAR TRANSISTOR (PNP)

Typical Characteristics

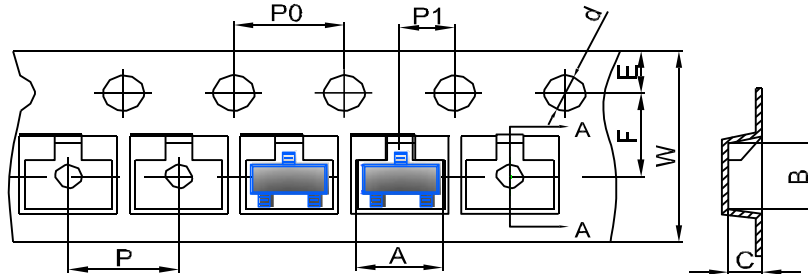


BIPOLAR TRANSISTOR (PNP)
SOT-23 Package Outline Dimensions


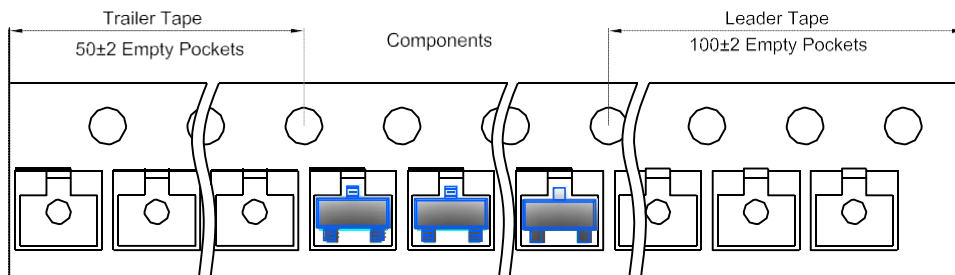
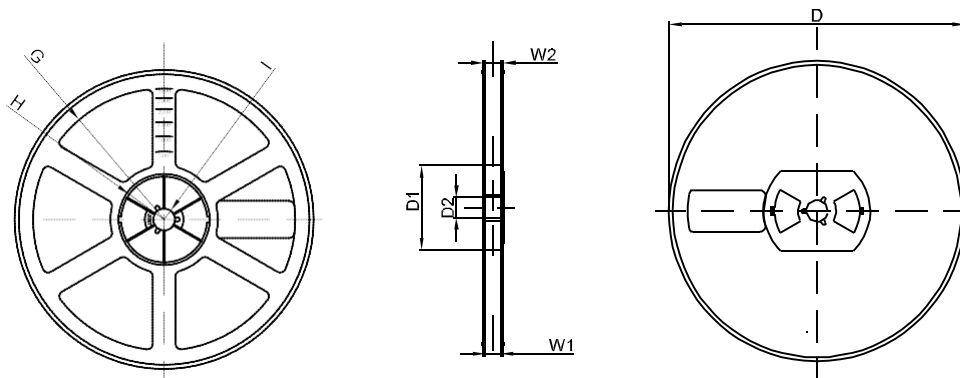
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

BIPOLAR TRANSISTOR (PNP)
SOT-23 Tape and Reel
SOT-23 Embossed Carrier Tape


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer

SOT-23 Reel


DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1

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